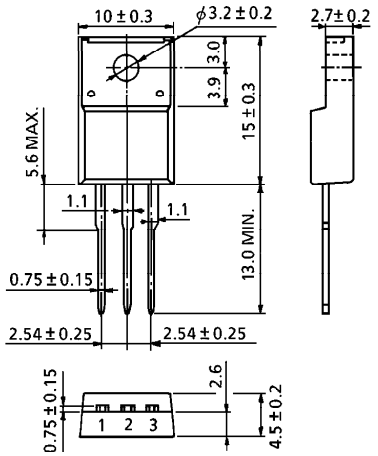
TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1887

HIGH CURRENT SWITCHING APPLICATIONS

Unit in mm

- Low Collector Saturation Voltage
  : $V_{CE\ (sat)} = -0.4V$ (Max.) at $I_C = -5A$



JEDEC	—
EIAJ	SC-67
TOSHIBA	2-10R1A

Weight : 1.7g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	−80	V
Collector-Emitter Voltage		V_{CEO}	−50	V
Emitter-Base Voltage		V_{EBO}	−7	V
Collector Current		I_C	−10	A
Collector Power Dissipation	Ta = 25°C	P_C	2.0	W
	Tc = 25°C		25	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = -70V$, $I_E = 0$	—	—	−1	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -7V$, $I_C = 0$	—	—	−1	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)\ CEO}$	$I_C = -10mA$, $I_B = 0$	−50	—	—	V
DC Current Gain		h_{FE}	$V_{CE} = -1V$, $I_C = -1A$	120	—	400	
Saturation Voltage	Collector-Emitter	$V_{CE\ (sat)}$	$I_C = -5A$, $I_B = -0.25A$	—	−0.2	−0.4	V
	Base-Emitter	$V_{BE\ (sat)}$	$I_C = -5A$, $I_B = -0.25A$	—	−0.95	−1.4	
Transition Frequency		f_T	$V_{CE} = -1V$, $I_C = -1A$	—	45	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = -10V$, $I_E = 0$, f = 1MHz	—	215	—	pF

961001EAA2

- TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.